Form PTO-1449 (REV. 2-32) U.S. Department of Commerce Patent and Trademark Office

INFORMATION DISCLOSURE STATEMENT BY APPLICANT
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Atty. Docket No.	Serial No.
A110-US	09/800,213
Applicant: John H. Coleman	
Filing Date: March 6, 2001	Group: 2826

U.S. PATENT DOCUMENTS

*Exam. Init.		Document No.	Date	Name	Class	Subclass	Filing Date if Appropriate
MLT		5,191,371	03-30-93	Li	437	11	
MLT		5,631,174	05-27-97	Li	438	475	
MLT		5,034,343	07-23-91	Rouse et al.	437	86	
MLT		5,374,564	12-20-94	Bruel	437	24	
MLT		5,461,245	10-24-95	Gribnikov et al.	257	197	
MLT		6,144,072	11-7-00	Iwamatsu et al.	257	347	1-15-99

FOREIGN PATENT DOCUMENT

		Document No.	Date	Country	Class	SubClass	Translator Yes	Translator No

OTHER DOCUMENTS (including Author, Title Date, Pertinent Pages, Etc.)

MLT			Jianming Li et al., Properties of Silicon-on-Defect-Layer Material, in: Materials Research Society Symposium Proceedings Vol. 396, David B. Poker et al., Ed., pp.745-750
MLT			Jianming Li, New annealing processes and explanation for novel silicon pn junctions formed by proton implantation, Electronics Letters, Vol. 35 (1997), pp. 133-134

Examiner: Minhloan Tran Date Considered: 12/04

* Examiner: Initial citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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MLT			Jianming Li et al., Properties of proton-implanted p-type Si: supports for the model explaining a novel p-n junction in Si, Nuclear Instruments and Methods in Physics Research B 160 (2000), pp. 190-193
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